

General Description

The WSP4409A is the highest performance trench P-Ch MOSFET with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WSP4409A meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% EAS Guaranteed
- Green Device Available

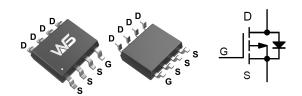
Product Summery

BVDSS	RDSON	ID
-30V	8.0mΩ	-15A

Applications

Power Management in Notebook Computer,
 Portable Equipment and Battery Powered Systems.
 HBM ESD protection level pass 8KV.

SOP-8 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units	
V_{DS}	Drain-Source Voltage	-30	V	
V_{GS}	Gate-Source Voltage	±20	V	
I _D @T _c =25℃	Continuous Drain Current, V _{GS} @ -10V ¹	-15	Α	
I _D @T _c =70°C	Continuous Drain Current, V _{GS} @ -10V ¹	-10	А	
I _{DM}	Pulsed Drain Current ²	-70	Α	
EAS	Single Pulse Avalanche Energy ³	70	mJ	
I _{AS}	Avalanche Current	-38	Α	
P _D @T _A =25°C	Total Power Dissipation⁴	2.5	W	
T _{STG}	Storage Temperature Range	-55 to 150	$^{\circ}$	
T_J	Operating Junction Temperature Range -55 to 150		${\mathbb C}$	

Thermal Data

Symbol	Parameter	Тур.	Max.	Unit
R _{θJA}	Thermal Resistance Junction-Ambient ¹		62.5	°C/W
$R_{ heta JC}$	Thermal Resistance Junction-Case ¹		24	°C/W



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30			V
$\triangle BV_{DSS}/\triangle T_{J}$	BV _{DSS} Temperature Coefficient	Reference to 25℃ , I _D =-1mA		-0.018		V/℃
D	Static Drain-Source On-Resistance ²	V _{GS} =-10V , I _D =-15A		8	10	0
R _{DS(ON)}		V _{GS} =-4.5V , I _D =-10A		10	14	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V =V 1 = 250··A	-1.0	-	-2.7	V
$\triangle V_{GS(th)}$	V _{GS(th)} Temperature Coefficient	$V_{GS}=V_{DS}$, $I_D=-250uA$		5.04		mV/℃
	Drain Source Loakage Current	V_{DS} =-24V , V_{GS} =0V , T_J =25 $^{\circ}\mathrm{C}$			-1	
I _{DSS}	Drain-Source Leakage Current	V_{DS} =-24V , V_{GS} =0V , T_J =55 $^{\circ}\mathrm{C}$			-5	· uA
I _{GSS}	Gate-Source Leakage Current	V_{GS} = $\pm 20V$, V_{DS} = $0V$			±100	nA
gfs	Forward Transconductance	V _{DS} =-5V , I _D =-10A		15		S
Q_g	Total Gate Charge (-4.5V)			72		
Q_{gs}	Gate-Source Charge	V _{DS} =-15V,V _{GS} =-4.5V,I _D =-15A		12		nC
Q_{gd}	Gate-Drain Charge			16		
T _{d(on)}	Turn-On Delay Time			16		
Tr	Rise Time	V_{DD} =-15V, V_{GS} =-10V, R_{G} =6 Ω ,		21		no
$T_{d(off)}$	Turn-Off Delay Time	I _D =-1A ,RL=15Ω		80		ns
T _f	Fall Time		14			
C _{iss}	Input Capacitance			3500		
Coss	Output Capacitance	V _{DS} =-15V , V _{GS} =0V , f=1MHz		635		pF
C _{rss}	Reverse Transfer Capacitance			645		

Guaranteed Avalanche Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
EAS	Single Pulse Avalanche Energy ⁵	V _{DD} =-25V , L=0.5mH , I _{AS} =-38A	30			mJ

Diode Characteristics

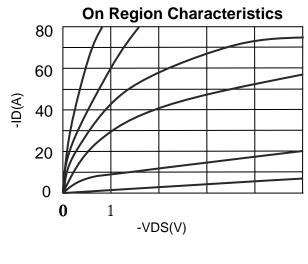
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
I _S	Continuous Source Current ^{1,6}	V _G =V _D =0V , Force Current			-4.0	Α
I _{SM}	Pulsed Source Current ^{2,6}				-70	Α
V_{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =-1A , T _J =25℃			-1.3	V
t _{rr}	Reverse Recovery Time	-IF=-17.6A,dI/dt=100A/μs,T _J =25℃		26		nS
Qrr	Reverse Recovery Charge			18		nC

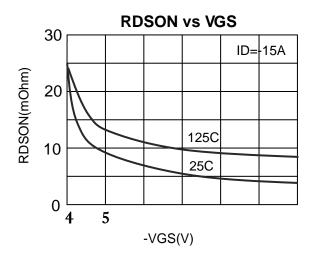
Note:

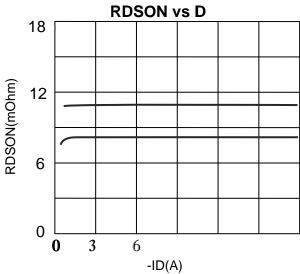
- 1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, t<10sec.
- 2.The data tested by pulsed , pulse width $\,\leq\,300\text{us}$, duty cycle $\,\leq\,2\%$
- 3.The EAS data shows Max. rating . The test condition is VDD=-25V,VGS=-10V,L=0.5mH,IAS=-38A
- 5.The Min. value is 100% EAS tested guarantee.
- 6. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

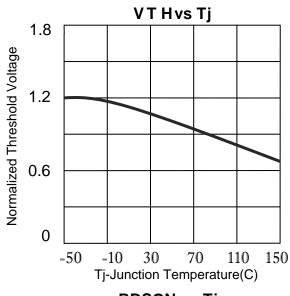


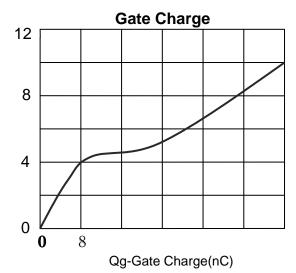
Typical Characteristics

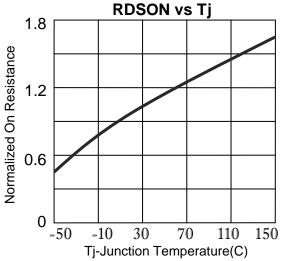




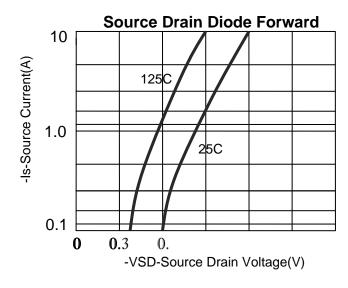


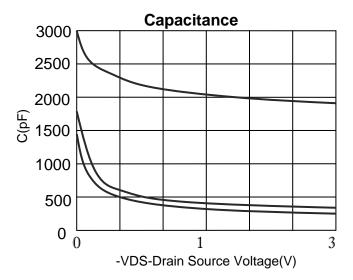


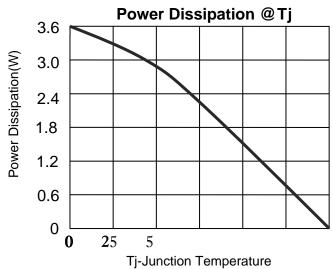


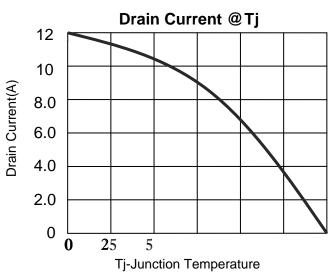


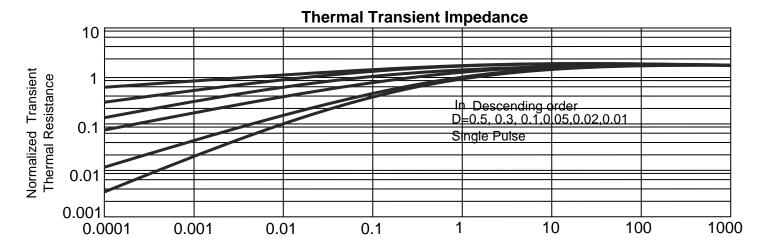














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